Excitation of surface plasmons at a SiO$_2$/Ag interface by silicon quantum dots: Experiment and theory

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The excitation of surface plasmons (SPs) by optically excited silicon quantum dots (QDs) located near a Ag interface is studied both experimentally and theoretically for different QD-interface separations. The Si QDs are formed in the near-surface region of an SiO$_2$ substrate by Si ion implantation and thermal annealing. Photoluminescence decay-rate distributions, as derived from an inverse Laplace transform of the measured decay trace, are determined for samples with and without a Ag cover layer. For the smallest, investigated Si-QDs-to-interface distance of 44 nm the average decay rate at $\lambda=750$ nm is enhanced by 80% due to the proximity of the Ag-glass interface, with respect to an air-glass interface. Calculations based on a classical dipole oscillator model show that the observed decay rate enhancement is mainly due to the excitation of surface plasmons that are on the SiO$_2$/Ag interface. By comparing the model calculations to the experimental data, it is determined that Si QDs have a very high internal emission quantum efficiency of $(77\pm17)\%$. At this distance they can excite surface plasmons at a rate of $(1.1\pm0.2)\times10^5$ s$^{-1}$. From the model it is also predicted that by using thin metal films the excitation of surface plasmons by Si QDs can be further enhanced. Si QDs are found to preferentially excite symmetric thin-film surface plasmons.

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I. INTRODUCTION

Silicon quantum dots (QDs) are crystalline clusters of 100–10 000 Si atoms that show quantum-confined luminescence at wavelengths in the visible or near infrared. Several microscale and nanoscale optoelectronic technologies based on Si QDs have been developed. Si-QD-based light-emitting diodes have been demonstrated as well as nonvolatile memory devices based on charge storage in Si QDs. Also it has been suggested that optical gain from Si QDs may lead to the fabrication of a Si-based laser (i.e., fully compatible with Si integrated-circuit manufacturing). The use of Si QDs in many of these optoelectronic devices requires precise control over their luminescence properties in often quite complex optical geometries. As first suggested by Purcell in 1946, the spontaneous emission rate of an emitter not only depends on the electronic transition probability, but also on its dielectric surrounding. In dielectrics this is described by the local optical density of states (DOS). In the most simple dielectric environment, a single dielectric interface, the DOS varies with the distance from the interface, which can result in a modification of the spontaneous emission rate for an optical emitter near the interface. For an optical emitter near a metal, additional decay processes can occur, such as surface plasmon (SP) or lossy surface wave excitation that modify the spontaneous emission.

In this paper we study the coupling between Si QDs embedded in SiO$_2$ and a Ag film. We measure the decay-rate distribution of the Si QDs. By varying the distance between the Si QDs and the Ag we demonstrate that Si QDs show an increased average decay rate that is mainly due to the excitation of SPs. By comparing our experimental results to model calculations, we determine the excitation rate of the SPs. As we will discuss, excitation of SPs that are subse-

<table>
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<tr>
<th>Energy (keV)</th>
<th>$R_p$ (nm)</th>
<th>$\sigma$ (nm)</th>
<th>Fluence (Si/cm$^2$)</th>
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<td>18</td>
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<tr>
<td>400</td>
<td>593</td>
<td>132</td>
<td>$9.3\times10^{16}$</td>
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TABLE I. Implantation conditions for the four Si-implanted samples, the projected range ($R_p$) and straggle ($\sigma$) were calculated.
A. Quantitative analysis of stretched-exponential decay

For a quantitative comparison of Si QD PL decay rate measurements it is important to realize that the time decay of the Si QD emission at a given detection wavelength is not described by a single decay rate, but rather a distribution of decay rates.\textsuperscript{15-17} This distribution reflects a variation in the Si QD emission characteristics, which can be caused by several factors.

1. The large linewidth of the emission of individual Si QDs at room temperature\textsuperscript{18,19} leads to a distribution of decay rates at a given emission wavelength.

2. Variations in the amount of interaction between Si QDs cause a distribution of decay rates. The interaction, which can cause quenching, is sensitive to variations in the nearest-neighbor distance. The distribution of nearest-neighbor distances is determined by small-scale inhomogeneities due to the nature of the nucleation and growth process of the Si QDs and large-scale variations in Si concentration (as for the Gaussian implantation depth profiles used here).\textsuperscript{16,20}

3. Si QDs with identical emission wavelengths may have varying degrees of surface passivation and thus different nonradiative decay rates.\textsuperscript{21}

4. Si QDs with identical emission wavelengths may have slightly different geometrical shapes and/or strains\textsuperscript{22} and thus a different decay rate.

5. Charge trapping at defect states causes intermittent Si QD emission (blinking) and thus leads to a variation in decay rate.\textsuperscript{2,23}

6. Pump power dependent decay processes can cause variations of the decay rate for Si QDs emitting at a fixed wavelength.\textsuperscript{20,23}

7. Identical Si QDs located at different positions in their photonic environment will experience a different decay rate due to spatial variations in both the local density of states and nonradiative processes, as will be discussed in this paper.

The combination of all, or some, of the above-mentioned effects result in a nonsingle exponential decay of the Si QD population. As an example of the nonsingle-exponential Si QD decay, Fig. 1 shows a Si QD PL decay trace measured at $\lambda=750$ nm for the shallowest Si implant ($R_p=44$ nm) on a part of the sample not covered with Ag. At $t=0$ the laser is switched off and a stretched exponential PL decay can be observed. The solid line shows a stretched exponential fit of the data, which corresponds to the decay rate distribution shown in the inset.

FIG. 1. PL decay measured at $\lambda=750$ nm for the shallowest Si implant ($R_p=44$ nm) on a part of the sample not covered with Ag. At $t=0$ the laser is switched off and a stretched exponential PL decay can be observed. The solid line shows a stretched exponential fit of the data, which corresponds to the decay rate distribution shown in the inset.

\[ e^{-(t/\tau_{\text{exp}})^\beta} = \int_0^\infty e^{-\tau/\tau_{\text{exp}}} \rho(\tau)d\tau. \]  \hspace{1cm} (1)

Using substitutions: $s=tt_{\text{exp}}$, $x=t_{\text{exp}}/\tau=\hat{W}/W_{\text{exp}}$, and $\lambda(x,\beta)=(t_{\text{exp}}/x^2)\rho(t_{\text{exp}},x)$, and $W$ the decay rate, the integral can be rewritten into a standard Laplace integral

\[ e^{-s\beta} = \int_0^\infty e^{-sx}\lambda(x,\beta)dx, \]  \hspace{1cm} (2)

with $\lambda(x,\beta)$ the rate distribution. The function $\lambda(x,\beta)$ can be written analytically\textsuperscript{27} as a series solution.
Decay rate distribution is divergent, an average decay rate is obtained from the stretched-exponential decay fit was obtained by transforming to recalculate the decay trace. Perfect agreement of the data in Fig. 2(b) with the stretched-exponential decay fit parameter \( \beta \) (circles) is plotted in the inset. To verify the correctness of our procedure, the obtained distribution was then Laplace transformed to recalculate the decay trace. Perfect agreement with the stretched-exponential decay fit was obtained (identical drawn curves in Fig. 1). Since the first moment of the decay rate distribution is divergent, an average decay rate cannot be calculated. However, since the average lifetime \( \langle \tau \rangle \) can be calculated, we approximate the average decay rate by

\[ \langle W \rangle = \langle \tau \rangle^{-1} = \frac{\beta}{\tau_{\text{exp}}} \Gamma^{-1}(\beta^{-1}). \]

In the remainder of this paper, the thus defined average decay rate will be used to compare the decay rates of different samples.

To explore the relation between the parameters of the stretched exponential function and the corresponding decay-rate distribution, we examine a characteristic Si QD emission spectrum for the sample with the deepest Si implant and not covered with Ag. Figure 2(a) shows the Si QD PL emission spectrum for the sample implanted with 400 keV Si at various emission wavelengths (dotted horizontal lines) the PL decay was measured and fitted using a stretched-exponential decay. The rate distributions, obtained from the fits, are plotted in Fig. 2(b) for six different emission wavelengths. The rate distributions are shifted vertically to match with the dashed lines in Fig. 2(a) to indicate the emission wavelengths at which the PL decay was measured. It can be clearly seen that the rate distribution shifts to lower rates as the emission wavelength increases. This is attributed to a combined effect of a DOS effect that causes the decay rate to increase with frequency and a decreasing exciton recombination probability with increasing QD size.\(^{28}\) From the rate distributions two quantities were calculated: the average decay rate and the inverse of the full width at half maximum (FWHM) normalized to the average decay rate \([1/(\langle \tau \rangle \text{FWHM})]\). Figure 2(c) shows the average decay rates (triangles), again showing the decreasing trend with increasing emission wavelength. For comparison, the decay rates obtained from the stretched-exponential fit \((1/\tau_{\text{exp}})\) are also plotted (circles). Both parameters follow a similar trend, although at slightly different absolute values, which is due to the way the width of the distribution affects the average decay rate. The decay rates are in the range of \((1–4) \times 10^4 \text{ s}^{-1}\), typical values for Si QDs made by ion-implantation.\(^{16,29}\) Figure 2(d) shows the inverse of the relative width of the distributions (triangles), derived from the data in Fig. 2(b). For comparison, \( \beta \) values from the corresponding stretched-exponential fit are also shown (circles). The parameter \( \beta \) is in the range of 0.55–0.7, which are typical values for Si QDs made by ion implantation.\(^{16}\) Both parameters in Fig. 2(d) show the same trend with wavelength, reflecting that a small value of \( \beta \) corresponds to a large distribution width, the typical characteristic of a stretched-exponential function.

**B. Optical characterization**

Figure 3(a) shows the normalized PL spectra for the samples with Si QDs located at four different depths from the interface for the sample in air (a) and covered with Ag (b). The spectra are shifted vertically to facilitate their comparison. The emission spectra are typical of quantum-confined emission from Si QDs. For large implantation depths the emission peaks at 775 nm (1.6 eV), which corresponds to a Si QD diameter of 3.8 nm.\(^{30}\) The width of the emission spectrum is 290 meV (FWHM). Measurements on single Si QDs show a linewidth of 120–210 meV,\(^{18}\) implying that the linewidth observed here is due to both the intrinsic Si QD emission spectrum width and inhomogeneous effects. While the spectrum of the three deepest implants peak at a similar wavelength, the spectrum from the Si QDs closest to the interface is significantly blueshifted. We attribute this shift, which reflects a smaller Si QD size, to a different...
Si QD nucleation and growth mechanism caused by the small width of the distribution or the proximity of the interface, which may lead to a different QD size distribution. PL spectra for the sample covered with Ag [Fig. 3(b)] show the same trend as for the sample in air, with a blueshift observed for the shallowest Si implant.

With the decay-rate distributions determined in a systematic way, as in Fig. 2, and by measuring the Si QD decay rate in the low pump power limit (where the decay rate is independent of pump power), the influence of the Ag layer on the PL decay rate of Si QDs in SiO2 can be quantified by calculating and comparing the average decay rate for the two interfaces. Figure 4 shows the decay rate distributions for the four samples with different Si implantation depths. The rate distributions are calculated from the PL decay traces measured at a PL emission wavelength of 750 nm, both for the sample in air (a) and covered with Ag (b). The arrows indicate the average decay rates determined as described in Sec. III A. For the air-covered sections, the decay rate distributions have an average of $(1.2-1.4) \times 10^4$ s$^{-1}$ and show no dependence on the depth. The same samples covered with Ag show a similar average decay rate for the three deepest Si implantations. However, for the shallowest Si implant the average decay rate near the Ag is significantly larger $(2.2 \times 10^4$ s$^{-1}$) as compared to the decay rates found on the same sample but without the presence of the Ag. Note that on the logarithmic scale in Fig. 4 the effect of the Ag layer may appear relatively small, but with the analysis introduced above we can now clearly conclude that the presence of the Ag enhances the average PL decay rate of Si QDs for the shallowest implant. For this sample the average decay rate increases from $(1.25 \pm 0.05) \times 10^4$ s$^{-1}$ for the air-covered section to $(2.2 \pm 0.2) \times 10^4$ s$^{-1}$ for the Ag-covered section, an enhancement by a factor $1.8 \pm 0.2$. It is also clear from Fig. 4(b) that for the shallowest Si implant the presence of Ag increases the width of the decay rate distribution.

C. Modeling the Si QD decay

The decay rate of an oscillating dipole in a (metallo-) dielectric environment can be calculated using a classical model as developed by Ford and Weber.31 In brief, the model calculates the decay rate of a dipole by determining the electric field at its position. The total electric field at the position of the dipole is the result of the dipolar field and the fields reflected from the dielectric surrounding of the dipole. To calculate these fields, the dipolar electric field is Fourier transformed into its spatial wave-vector components. The fields resulting from reflections at the interfaces are then calculated for each wave vector using the Fresnel reflection coefficients of the interface, which are determined using the dielectric constants as input parameters. After integration over the out-of-plane wave vectors the electric field at the position of the dipole is a function of normalized in-plane wave vector only $(k_i/k_d)$, with $k_d=n_d \omega/c$ the magnitude of the wave vector of a plane wave in the dielectric as determined by the optical frequency $\omega$ of the spontaneous emission and the refractive index $n_d$ of the dielectric. By taking
FIG. 5. Power dissipation as a function of in-plane wave vector for a randomly oriented dipole located near a SiO$_2$/air interface, emitting at $\lambda=750$ nm, for a distance of 44 nm (a) and 593 nm (b) to the interface. (c)-(f) The same calculation, but for a SiO$_2$/Ag interface and distances of 44, 193, 401, and 593 nm to the interface. The wave-vector region $k_d/k_g<1$ corresponds to spontaneous emission, $1<k_d/k_g<1.158$ to SP excitation and $k_d/k_g>1.158$ to lossy surface wave excitation. The different wave-vector ranges are indicated in (c) with different fill patterns.

The imaginary part of the product of the electric field at the position of the dipole and the dipole moment, the power dissipation can be calculated at any normalized in-plane wave vector. Integrating the power dissipation over all in-plane wave vectors divided by the photon energy $\hbar\omega$ then yields the total decay rate of the dipole. In this analysis the parallel and perpendicular dipole orientations relative to the interface are treated separately. They are then averaged to obtain the decay rate for a randomly oriented dipole, as is the case for Si QDs in the amorphous SiO$_2$ host.

In our analysis we use the dielectric constants of Ag ($\varepsilon_{Ag}=\varepsilon_{Ag}^\prime+i\varepsilon_{Ag}^\prime\prime=-15+i0.86$) and SiO$_2$ ($\varepsilon_{SiO_2}=2.1$) at $\lambda=750$ nm to calculate the power dissipation of a randomly oriented dipole as a function of normalized in-plane wave vector for a given distance from the interface. Figure 5(a) shows the result for a dipole at 44 nm from an SiO$_2$/air interface. This distance corresponds to the peak position of the shallowest Si implant. Power is dissipated for $k_d/k_g<1$ corresponding to spontaneous emission in the SiO$_2$ and air regions. In this wave-vector range $k_d<k_g$ so that far-field plane waves with a real wave vector perpendicular to the interface are allowed. The small wiggle at $k_d/k_g\sim0.69$ is due to the difference in power dissipation for wave vectors in air ($k_d/k_g<0.69$) and SiO$_2$ ($k_d/k_g<1$). Figure 5(b) shows a similar calculation, but now for a dipole at 593 nm from the interface. Due to the larger distance interference wiggles are observed that are due to constructive or destructive interference of the reflected dipolar field, which either increases or decreases the dipole’s power dissipation for a particular wave vector. The total power dissipation for the two depths, i.e., the integral over the power dissipation spectra in Figs. 5(a) and 5(b), is nearly identical. This is due to the relatively small reflection at the SiO$_2$/air interface. Figure 5(c) shows a similar calculation as for Fig. 5(a) (dipole located at 44 nm), but for the SiO$_2$/Ag interface. Again, power is dissipated for $k_d/k_g<1$, corresponding to spontaneous emission into the far field. However, in contrast to the case for the SiO$_2$/air interface, power is also dissipated for larger wave vectors ($k_d/k_g>1$). In this wave-vector range $k_d>k_g$, so that the wave vector of the waves perpendicular to the interface must be fully imaginary. This leads to waves bound to the interface. First, a power dissipation resonance is observed for $k_d/k_g=1.078$, corresponding to the ratio $\sqrt{\varepsilon_{Ag}^\prime/\varepsilon_{Ag}^\prime\prime}$; the wave vector for a SP propagating along the SiO$_2$/Ag interface, normalized to the wave vector for a plane wave in SiO$_2$. The width of the resonance is determined by dissipation in the metal (represented by $\varepsilon_{Ag}^\prime\prime$, the imaginary part of the dielectric constant for Ag), which is relatively small at this wavelength (1/e SP intensity propagation length is $\sim8$ $\mu$m). A considerable amount of power is contained in the SP resonance (note the log scale). At larger wave vectors power is dissipated to lossy surface waves; all losses processes such as electron-hole excitation and electron scattering in the Ag. Similar calculations are performed for dipoles spaced 193, 401, and 593 nm from the SiO$_2$/Ag interface, and are shown in Figs. 5(d)-(f). The calculations show that the excitation rate of lossy surface waves decreases very rapidly as the distance increases. Also the excitation rate of SPs decreases, although less rapidly. Indeed, SP excitation is a near-field effect that, for optical wavelengths, is known to occur for distances up to $\sim100$ nm, while the dissipation into lossy surface waves typically occurs on a 10 nm length scale. Note that the wiggles observed for $k_d/k_g<1$ are more pronounced in the Ag covered sample than for the sample in air [Figs. 5(a) and 5(b)], due to the larger reflectivity of the interface. The minima and maxima occur at different wave vectors than for the SiO$_2$/air interface, owing to the different phase shifts that occur upon reflection from either the SiO$_2$/Ag or the SiO$_2$/air interface.

Since the various ranges of normalized in-plane wave vector in Fig. 5 represent different decay channels, the decay rate of the dipole into these channels can be obtained by an integration of the dissipated power over the corresponding wave-vector range, indicated with different fill patterns in Fig. 5(c): spontaneous emission: $k_d/k_g<1$, surface plasmon excitation: $1<k_d/k_g<2k_{SP}-1=1.158$, and lossy surface wave excitation: $k_d/k_g=1.158$. For a distance of 44 nm and an emission wavelength of 750 nm the SP excitation rate is calculated using three different methods: the above-mentioned integration over the wave-vector range, a full Lorentzian fit of the SP resonance, and using an approximation for the Ag reflection coefficient; all methods giving the same dissipated power. It should be noted that at wavelengths much closer to the SP resonance ($\lambda<500$ nm) and at much shorter distances ($d<10$ nm) from the interface the
wave-vector integration range is not a valid approximation for the SP excitation rate calculation. The result of this integration procedure is shown in Fig. 6 for a range of dipole distances from the interface. Figure 6(a) shows the distance dependent decay rate for a dipole near the SiO$_2$/air interface. The rate is normalized to unity for large distances from the interface. As can be seen, close to the interface the normalized decay rate is significantly lower than for a dipole in the bulk of the material. We attribute the fact that this is not observed in the decay rate distributions shown in Fig. 4(a) to the blueshift of the Si QD PL emission. This blueshift, which is shown in Fig. 3(a), represents a smaller average QD size that leads, due to the large emission linewidth of individual Si QD, to an increase of the average Si QD decay rate, which may thus compensate for the decrease of the decay rate by the DOS. The decay rate shows oscillating behavior as a function of distance, due to the interference of reflected waves with the direct dipole field that either increases or decreases the dipole’s dissipation rate. A similar effect was reported earlier in Refs. 7 and 33 for the case of 1.5 μm emission of Er$^{3+}$ ions near a SiO$_2$/air interface. Figure 6(b) shows the calculated decay rates for the dipole in proximity to the SiO$_2$/Ag interface. The contributions of spontaneous emission, SP excitation, and lossy surface wave (LSW) excitation. In (c) the Si depth distributions are plotted for the four implants.

FIG. 6. Normalized decay rate as a function of distance from a SiO$_2$/air interface (a) and an SiO$_2$/Ag interface (b). For the SiO$_2$/Ag interface sample the total decay rate is divided into its three constituent parts: spontaneous emission, SP excitation, and lossy surface wave (LSW) excitation. In (c) the Si depth distributions are shown for the four implants.

Finally, we discuss the large difference in β for the two interfaces, observed in Fig. 4 for the shallowest Si implant. Figure 6 shows that for the shallowest Si implant the decay rates for the SiO$_2$/Ag interface depend strongly on depth than for the SiO$_2$/air interface: the variation of decay rate with depth differs by a factor of 5 at the Si peak position. This leads to a larger spread of Si QD decay rates for the SiO$_2$/Ag interface, and consequently a decrease in β, as is observed.
The presented results show that optically active Si QDs can efficiently excite SPs on a SiO$_2$/Ag interface. For most optimal excitation of SPs the Si QDs should be located at ~40 nm from the SiO$_2$/Ag interface, where SP coupling is strong and loss processes are relatively small. Coupling to SPs provides a unique way to enhance the effective emission rate and QE of Si QDs. By exciting SPs at a rate $W_{sp}$ and then coupling the SPs out into the far field, the SP excitation that initially constitutes a loss process may be turned into a radiative process. In this way the radiative decay rate $W_{rad}$ can be artificially enhanced to $W_{rad} + W_{sp}$. Similarly, for optical emitters with an internal QE $<1$, coupling to SPs and subsequent out coupling to the far field, can enhance the internal QE. Optimized geometries have shown SP out-coupling efficiencies close to unity.

In the present experiment the SP generation efficiency is 60% for the shallowest Si implant (see Fig. 6), limiting the maximum achievable increase in emission rate and QE. Here we discuss different ways to increase the SP excitation rate. The largest coupling of a dipole to SPs is achieved when the emission frequency matches the SP resonance frequency, i.e., the frequency for which $\varepsilon_{metal} = -\varepsilon_d$. In the present case, for an emission wavelength of 750 nm, the large discrepancy between the dielectric constant of the SiO$_2$ ($\varepsilon_{SiO_2} = 2.1$) and the Ag ($\varepsilon_{Ag} = -15 + 0.86$), results in a relatively small SP coupling rate. Using an alternative host for Si QDs that has a higher dielectric constant will increase the coupling. For example, for a dipole at 44 nm from the interface, emitting at 750 nm with Ag as a metal and Si$_3$N$_4$ ($\varepsilon = 4$) as a dielectric matrix, 63% of the dipole’s excitation energy is converted into SPs.

The SP coupling rate can be further enhanced by modifying the SP dispersion relation by changing the thickness of the metal. For a metal layer with a thickness of the same order of magnitude as the skin depth, SPs propagating at both sides of the metal interact. This results in a splitting of the single SP mode into an asymmetric and symmetric mode. We calculated the thin metal film SP dispersion using Ford and Weber’s model. Calculations were performed for a multilayer structure consisting of an optically thick SiO$_2$ layer on top of a 10 nm thick Ag layer on top of a SiO$_2$ substrate, with the dipole at 44 nm distance from the Ag layer. The inset in Fig. 7 shows the power dissipation, calculated for a randomly oriented dipole emitting at 480 nm. Clearly, the two SP modes can be observed: the asymmetric SP mode at $k_d/k_{Ag} = 1.0083$, and the symmetric SP mode at $k_d/k_{Ag} = 5.08$. Similar calculations were performed over a large range of frequencies (taking the dispersion of $\varepsilon_{Ag}$ into account) and at each frequency the wave vectors of both modes were derived. The result is shown in Fig. 7, with the light line $\omega = kc/\sqrt{\varepsilon_d}$ shown for reference (“light line”). From these data we can observe that, at a given frequency, the wave vector for the symmetric SP mode, in comparison to the infinite Ag layer, is increased and the wave vector for the asymmetric SP mode is decreased. Since the SP mode density is proportional to $d(k^2)/d\omega$, decreasing the film thickness increases the SP mode density for the symmetric SP mode. For the case calculated in Fig. 7, this leads to a tenfold increase in the SP excitation rate. A full calculation of the thin-film SPs excitation rate should also take into account the overlap of the dipole field and the SP mode.

The present work shows that SP modes can be selectively excited by a strongly coupled dipole, with the symmetric mode being more pronounced for thin films compared to the asymmetric mode. Further work will address this in more detail. Given the fact that Si QDs can be electrically excited, this provides a way to electrically generate SPs.

In summary, we have shown that Si QDs can couple to surface plasmons at the Ag/SiO$_2$ interface, leading to an increase of their decay rate. The average photoluminescence decay rate of Si QDs in SiO$_2$ is enhanced by 80% when they are placed in close proximity (~40 nm) to a Ag interface. Calculations performed with a classical dipole oscillator model are in good agreement with the data. For the shallowest Si implant the surface plasmon excitation efficiency is 60% and amounts to a surface plasmon excitation rate of $(1.1 \pm 0.2) \times 10^4$ s$^{-1}$. From a comparison of the experimental decay-rate distributions to the model calculations, we determine the Si QD internal quantum efficiency to be $(77 \pm 17)\%$. We calculate that the surface plasmon excitation efficiency can be further enhanced by exciting surface plasmons on thin metal films, in which case the symmetric SP mode is preferentially excited. As Si QDs can be electrically excited, this work provides design criteria for an electrically pumped, mode selective, surface plasmon source.
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